



SPN1014

N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN1014 is the N-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

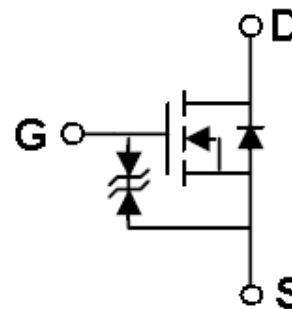
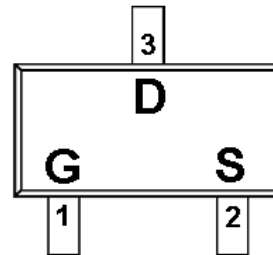
FEATURES

- ◆ N-Channel
20V/0.65A, $R_{DS(ON)}=380m\Omega@V_{GS}=4.5V$
20V/0.55A, $R_{DS(ON)}=450m\Omega@V_{GS}=2.5V$
20V/0.45A, $R_{DS(ON)}=800m\Omega@V_{GS}=1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-523 (SC-89) package design

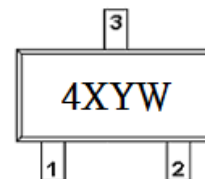
APPLICATIONS

- Drivers : Relays/Solenoids/Lamps/Hammers
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

PIN CONFIGURATION(SOT-523 / SC-89)



PART MARKING



Y : year
W: week



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PIN DESCRIPTION

Pin	Symbol	Description
1	G	Gate
2	S	Source
3	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN1014S52RG	SOT-523	4X
SPN1014S52RGB	SOT-523	4X

※ SPN1014S52RG : Tape Reel ; Pb – Free

※ SPN1014S52RGB : Tape Reel ; Pb – Free, Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit	
Drain-Source Voltage	V _{DSS}	20	V	
Gate –Source Voltage	V _{GSS}	±12	V	
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	0.65	A
		TA=80°C	0.45	
Pulsed Drain Current	I _{DM}	1.0	A	
Continuous Source Current(Diode Conduction)	I _S	0.3	A	
Power Dissipation	P _D	TA=25°C	0.27	W
		TA=70°C	0.16	
Operating Junction Temperature	T _J	-55/150	°C	
Storage Temperature Range	T _{STG}	-55/150	°C	



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ELECTRICAL CHARACTERISTICS

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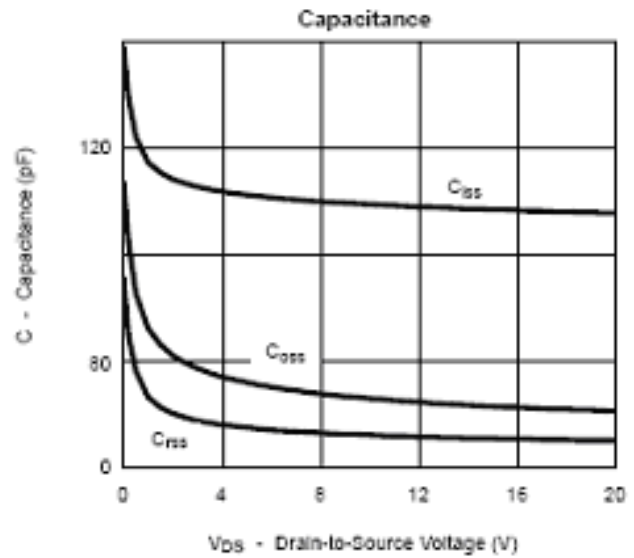
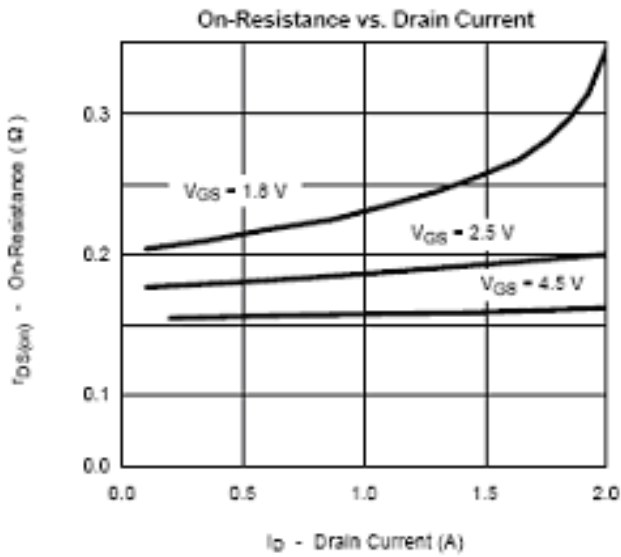
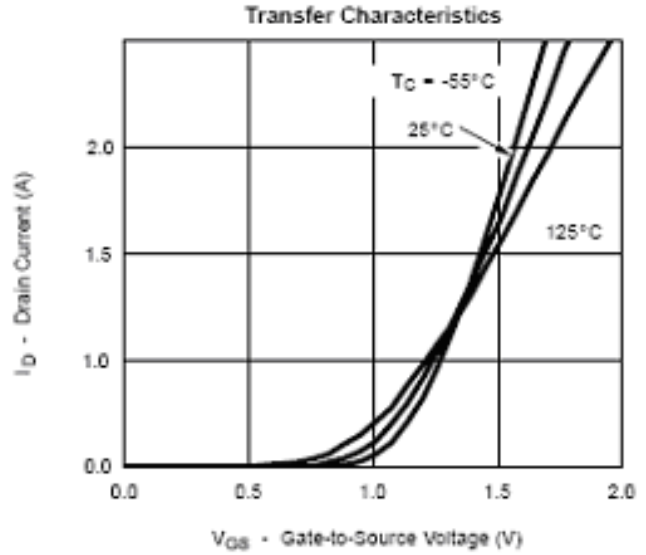
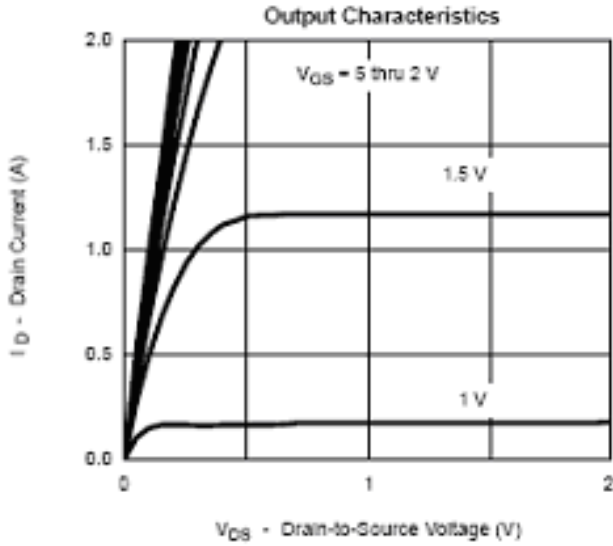
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.35		1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			30	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	μA
		$V_{DS}=16V, V_{GS}=0V$ $T_J=55^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 4.5V, V_{GS}=5V$	0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.65A$		0.26	0.38	Ω
		$V_{GS}=2.5V, I_D=0.55A$		0.32	0.45	
		$V_{GS}=1.8V, I_D=0.45A$		0.42	0.80	
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=0.4A$		1.0		S
Diode Forward Voltage	V_{SD}	$I_S=0.15A, V_{GS}=0V$		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V,$ $I_D=0.6A$		1.2	1.5	nC
Gate-Source Charge	Q_{gs}			0.2		
Gate-Drain Charge	Q_{gd}			0.3		
Turn-On Time	$t_{d(on)}$	$V_{DD}=10V, R_L=10\Omega,$ $I_D=0.5A$ $V_{GEN}=4.5V, R_G=6\Omega$		5	10	ns
	t_r			8	15	
Turn-Off Time	$t_{d(off)}$			10	18	
	t_f			1.2	2.8	



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TYPICAL CHARACTERISTICS

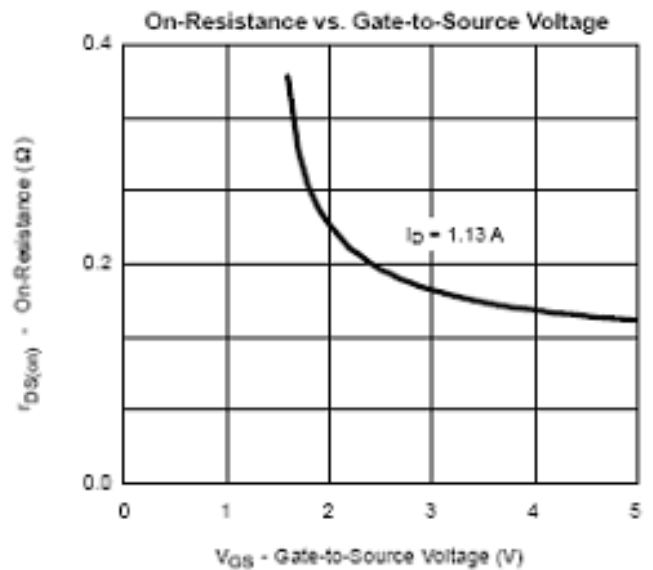
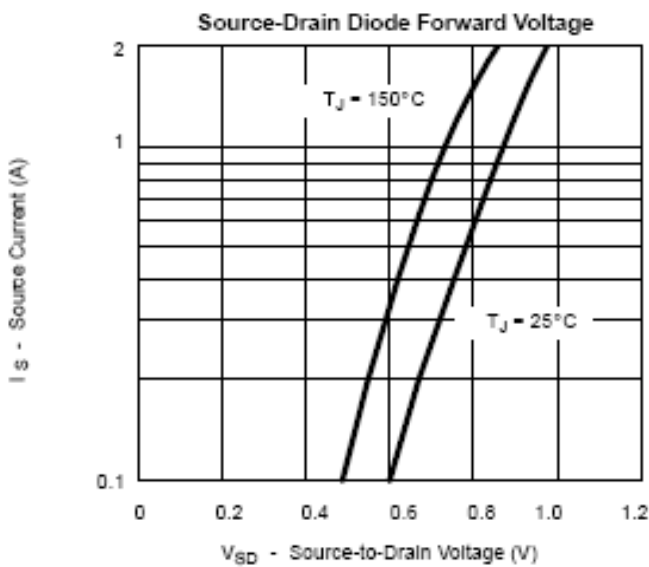
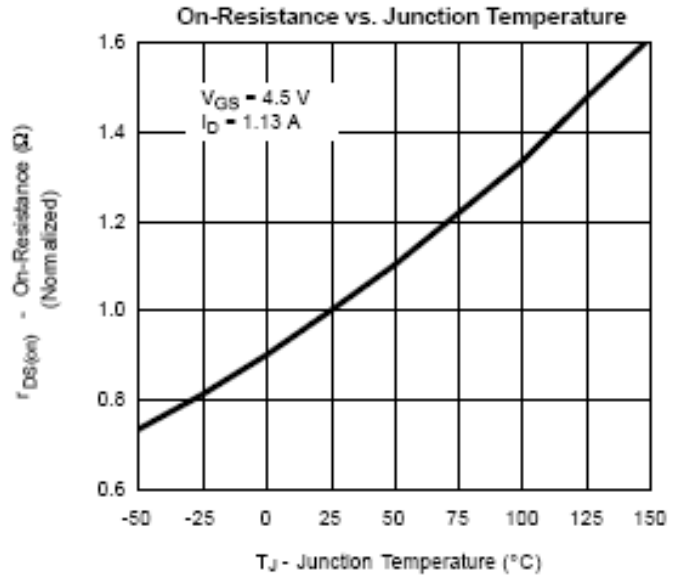
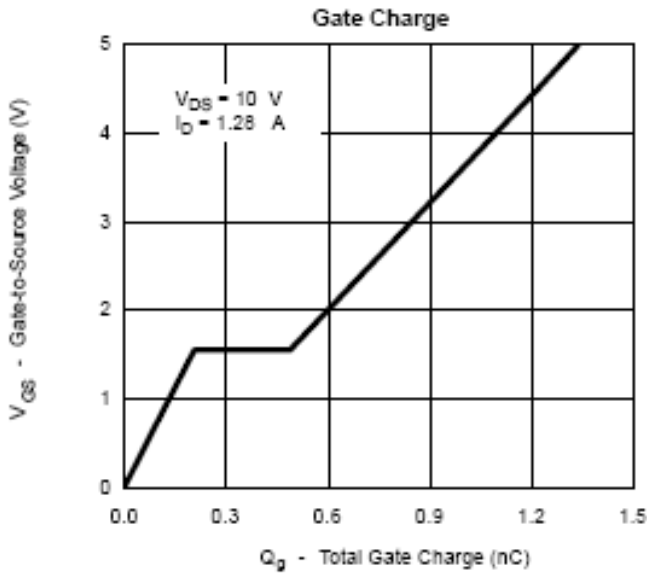




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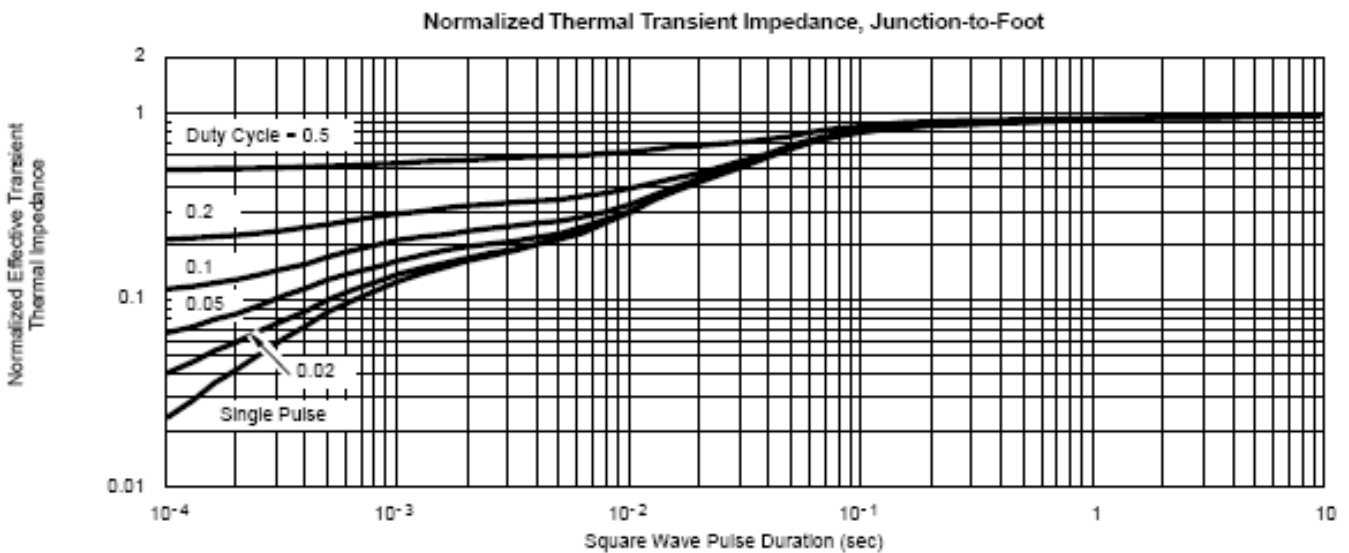
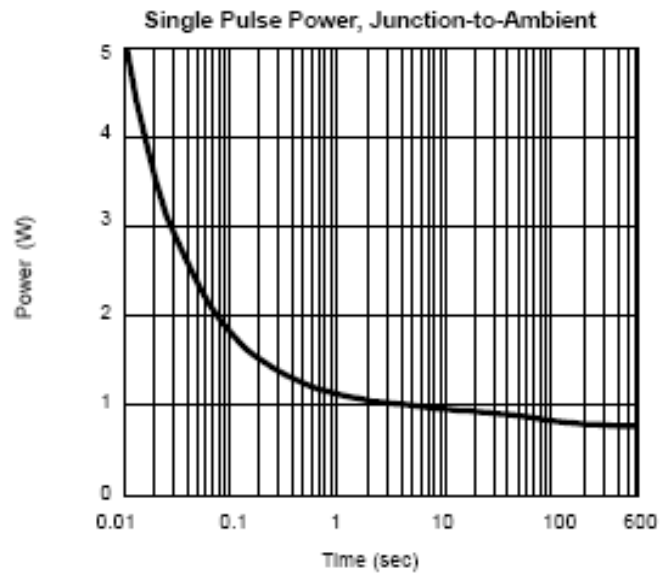
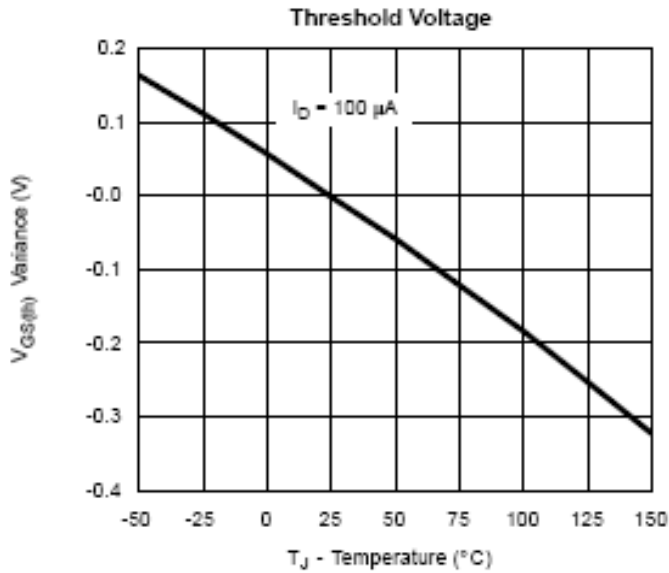




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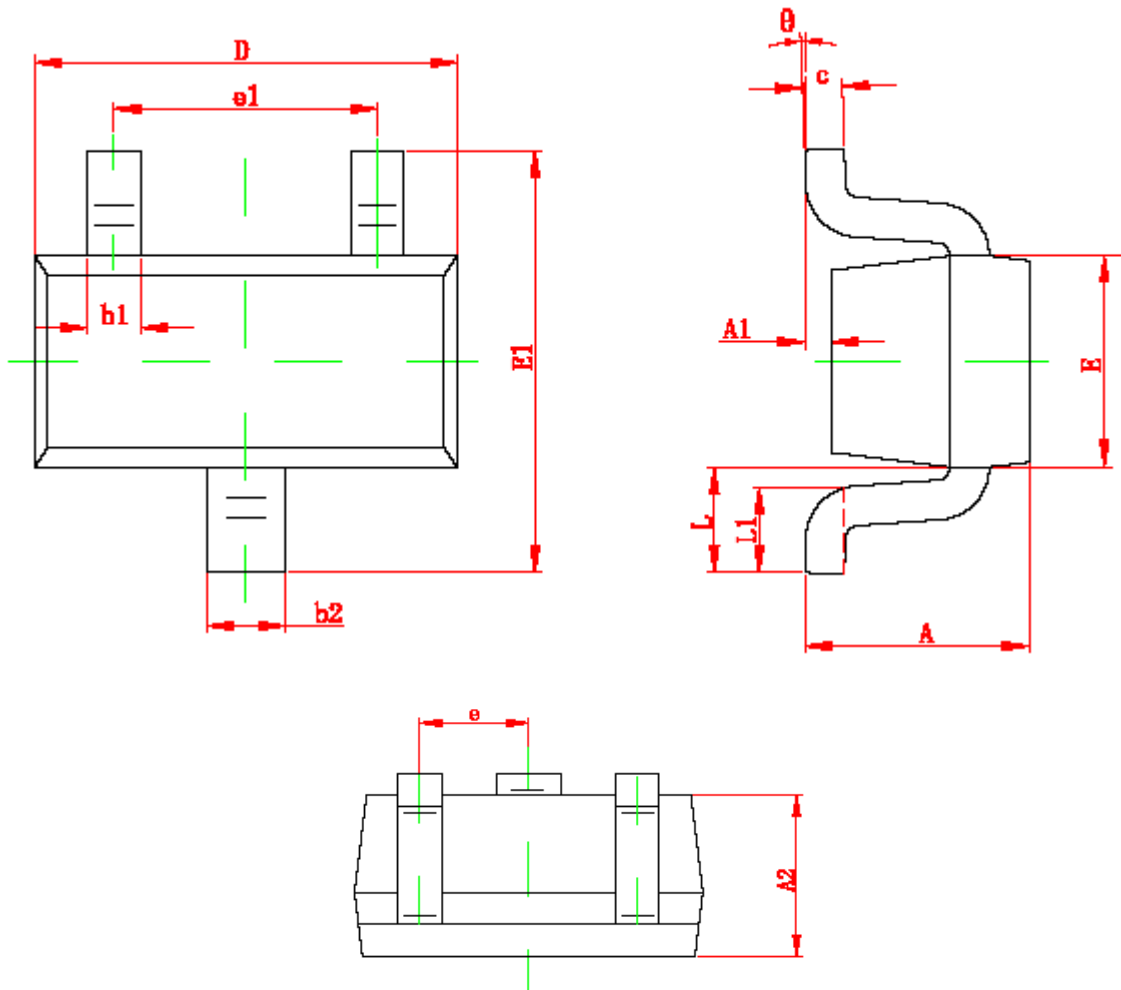




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SOT-523 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.325	0.010	0.013
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.750	0.850	0.030	0.033
E1	1.450	1.750	0.057	0.069
e	0.500 TYP		0.020 TYP	
e1	0.900	1.100	0.035	0.043
L	0.550 REF		0.022 REF	
L1	0.280	0.440	0.011	0.017
θ	0°	4°	0°	4°



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